

## High power NPN epitaxial planar bipolar transistor

#### **Features**

- High breakdown voltage V<sub>CEO</sub> = 140 V
- Complementary to 2STW1695
- Fast-switching speed
- Typical f<sub>t</sub> = 20 MHz
- Fully characterized at 125 °C

### **Applications**

■ Audio power amplifier

### **Description**

The device is a NPN transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stage.

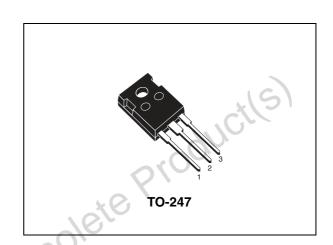


Figure 1. Internal schematic diagram

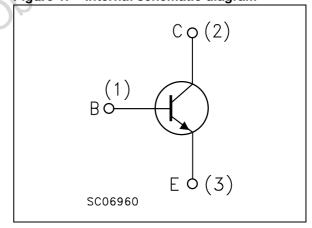


Table 1. Device summary

Order code	Marking	Package	Packaging
2STW4468	2STW4468	TO-247	Tube

Electrical ratings 2STW4468

# 1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-base voltage (I <sub>E</sub> = 0)	200	V
V <sub>CEO</sub>	Collector-emitter voltage (I <sub>B</sub> = 0)	140	V
V <sub>EBO</sub>	Emitter-base voltage (I <sub>C</sub> = 0)	6	V
I <sub>C</sub>	Collector current	10	Α
I <sub>CM</sub>	Collector peak current (t <sub>P</sub> < 5 ms)	20	А
P <sub>tot</sub>	Total dissipation at T <sub>c</sub> = 25 °C	100	W
T <sub>stg</sub>	Storage temperature	-65 to 150	°C
T <sub>J</sub>	Max. operating junction temperature	150	°C

Table 3. Thermal data

Obsolete Product(s)

Symbol	Parameter	Value	Unit
R <sub>thj-case</sub>	Thermal resistance junction-case max	1.25	°C/W

2STW4468 Electrical characteristics

# 2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$ 

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector cut-off current (I <sub>E</sub> = 0)	V <sub>CB</sub> = 200 V			0.1	μΑ
I <sub>EBO</sub>	Emitter cut-off current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 6 V			0.1	μΑ
V <sub>(BR)CEO</sub> <sup>(1)</sup>	Collector-emitter breakdown voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 50 mA	140	1	Cill:	V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage (I <sub>E</sub> = 0)	I <sub>C</sub> = 100 μA	200	000		V
V <sub>(BR)EBO (1)</sub>	Emitter-base breakdown voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 1 mA	6			V
V <sub>CE(sat)</sub> (1)	Collector-emitter saturation voltage	$I_C = 5 A$ $I_B = 50$ $I_C = 7 A$ $I_B = 70$			0.5 0.7	V V
V <sub>BE</sub>	Base-emitter voltage	$V_{CE} = 5 V$ $I_C = 5 A$	١		1.3	V
h <sub>FE</sub>	DC current gain	$I_C = 3 A$ $V_{CE} = 4$ $I_C = 5 A$ $V_{CE} = 4$			140	
f <sub>T</sub>	Transition frequency	$I_C = 0.5 \text{ A}$ $V_{CE} = 1$	2 V	20		MHz
C <sub>CBO</sub>	Collector-base capacitance (I <sub>E</sub> = 0)	V <sub>CB</sub> = 10 V f = 1 M	lHz	150		pF
×6,	Resistive Load					
t <sub>on</sub>	Turn-on time	$V_{CC} = 60 \text{ V}$ $I_C = 5 \text{ A}$	4	0.22		μs
t <sub>stg</sub>	Storage time	$I_{B1} = -I_{B2} = 0.5 A$		4.3		μs
t <sub>f</sub>	Fall time			0.5		μs

<sup>1.</sup> Pulse duration = 300  $\mu$ s, duty cycle  $\leq$  1.5 %

Electrical characteristics 2STW4468

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Output characteristics

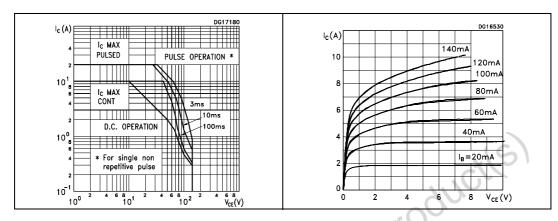


Figure 4. DC current gain

Figure 5. Collector-emitter saturation voltage

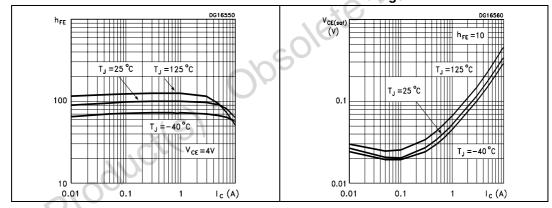
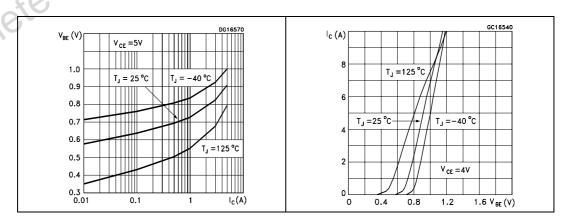


Figure 6. Base-emitter voltage

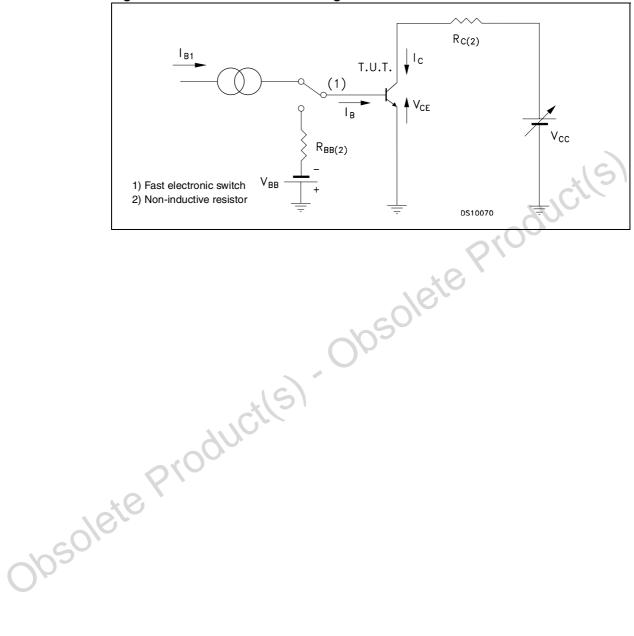
Figure 7. Base-emitter voltage



2STW4468 Electrical characteristics

### 2.2 Test circuit

Figure 8. Resistive load switching test circuit



## 3 Package mechanical data

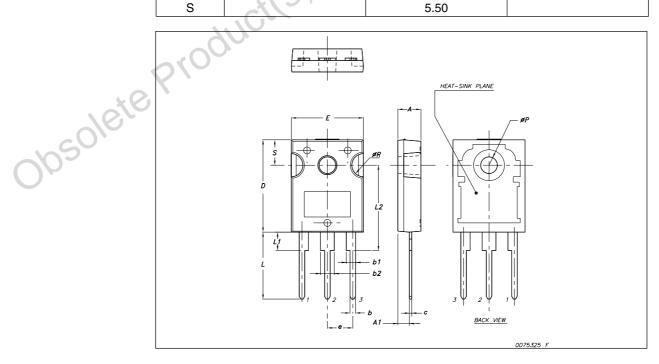
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Obsolete Product(s). Obsolete Product(s)

2STW4468

#### **TO-247 Mechanical data**

Dim.	mm.				
<b>D</b>	Min.	Тур	Max.		
Α	4.85		5.15		
A1	2.20		2.60		
b	1.0		1.40		
b1	2.0		2.40		
b2	3.0	3.40			
С	0.40		0.80		
D	19.85	Q.	20.15		
E	15.45	15.75			
е		5.45			
L	14.20	c0\-	14.80		
L1	3.70	75	4.30		
L2		18.50			
øΡ	3.55		3.65		
øR	4.50		5.50		
S		5.50			



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Revision history 2STW4468

# 4 Revision history

Table 5. Document revision history

Date	Revision	Changes
23-Oct-2006	1	Initial release
09-Feb-2007	2	New graphics
20-Feb-2007	3	Document status promoted from preliminary data to datasheet.
13-Oct-2008	4	Content reworked to improve readability, no technical changes.
olete Prod	ucils	Content reworked to improve readability, no technical changes.

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